

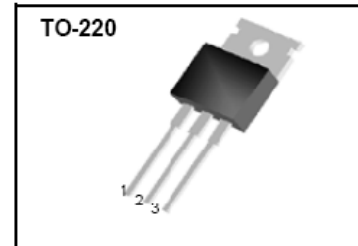
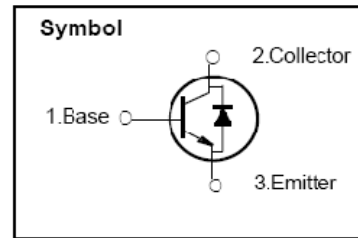
## High Voltage Fast-Switching NPN Power Transistor

### Features

- ◆ Very High Switching Speed
- ◆ Minimum Lot-to-Lot  $h_{FE}$  Variation
- ◆ Wide Reverse Bias SOA
- ◆ Built-in freewheeling diode

### General Description

This Device is designed for high voltage, High speed switching characteristics required such as lighting system, switching mode power supply.



### Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Units
$V_{CES}$	Collector-Emitter Voltage	$V_{BE} = 0$	700	V
$V_{CEO}$	Collector-Emitter Voltage	$I_B = 0$	400	V
$V_{EBO}$	Emitter-Base Voltage	$I_C = 0$	9.0	V
$I_C$	Collector Current		4.0	A
$I_{CP}$	Collector pulse Current		8.0	A
$I_B$	Base Current		2.0	A
$I_{BM}$	Base Peak Current	$t_P = 5ms$	4.0	A
$P_C$	Total Dissipation at $TC = 25^\circ C$		75	W
$T_J$	Operation Junction Temperature		- 40 ~ 150	$^\circ C$
$T_{STG}$	Storage Temperature		- 40 ~ 150	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance Junction to Case	1.67	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	62.5	$^\circ C/W$

# SBP13005D

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
I <sub>CEV</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V)	V <sub>CE</sub> = 700V V <sub>CE</sub> = 700V, T <sub>C</sub> = 100°C	-	-	1.0 5.0	mA
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>B</sub> = 0, I <sub>C</sub> = 10mA	400	-	-	V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.0A, I <sub>B</sub> = 0.2A I <sub>C</sub> = 2.0A, I <sub>B</sub> = 0.5A I <sub>C</sub> = 4.0A, I <sub>B</sub> = 1.0A	-	-	0.5 0.6 1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1.0A, I <sub>B</sub> = 0.2A I <sub>C</sub> = 2.0A, I <sub>B</sub> = 0.5A	-	-	1.2 1.6	V
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1.0A, V <sub>CE</sub> = 5V I <sub>C</sub> = 2.0A, V <sub>CE</sub> = 5V	10 10		40 30	
t <sub>s</sub> t <sub>f</sub>	Storage Time Fall Time	I <sub>C</sub> = 2.0A, V <sub>CC</sub> = 125V I <sub>B1</sub> = 0.4A, I <sub>B2</sub> = -0.4A T <sub>P</sub> = 25us	-	-	3.6 1.6	μs
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> =0.5A, V <sub>CE</sub> =10V	4	-	-	MHz
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> =2A	-	-	2.5	V
C <sub>OB</sub>	Output Capacitance	I <sub>C</sub> =0.5A, V <sub>CE</sub> =10V	-	6.5		pF

**Note:**

Pulse Test : Pulse width 300, Duty cycle 2%

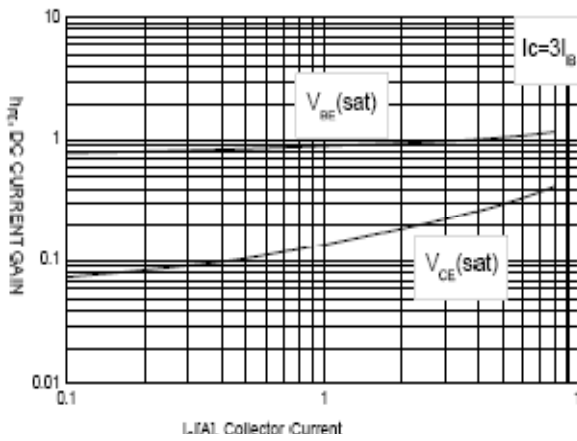


Fig. 1 DC Current Gain

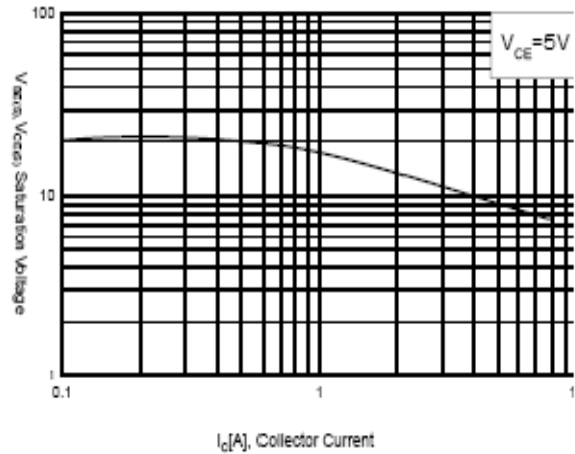


Fig. 2 Saturation Voltage

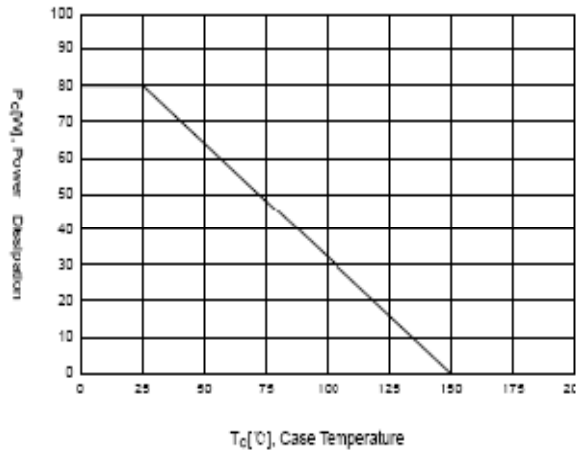


Fig. 3 Power Derating

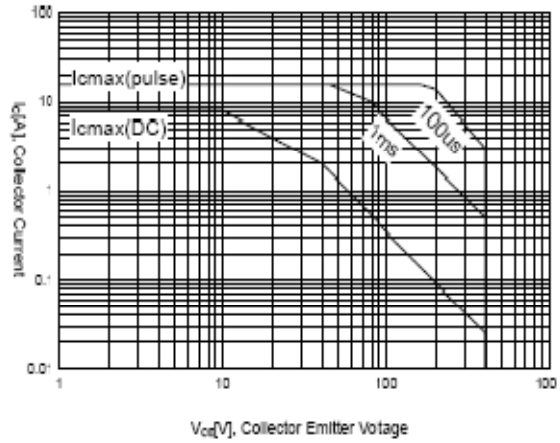


Fig. 4 Safe Operation Area

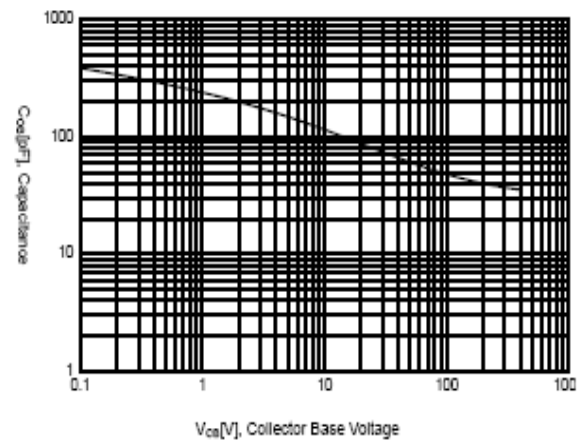


Fig. 5 Collect output capacitance

